

AMENDMENT TO THE CLAIMS

Please **AMEND** claims 1 and 13 as follows.

Please **CANCEL** claims 12 and 23-28.

Please **ADD** claims 29-34 as follows.

A copy of all pending claims and a status of the claims is provided below.

Claim 1. (currently amended) A method of fabricating a semiconductor structure, comprising the steps of:

forming a raised source region on a substrate;
forming a raised drain region on the substrate; and
forming a first silicon layer over the raised source region and a second silicon layer over the raised drain region,

wherein the first silicon layer formed over the raised source region and the second silicon layer over the raised drain region include cap portions and sidewall portions, the method further comprising a step of forming sacrificial spacers along the silicon sidewall portions.

Claim 2. (original) A method according to claim 1, wherein the substrate includes a SiGe layer atop a buried oxide layer.

Claim 3. (original) A method according to claim 1, further comprising a step of forming a gate stack on the substrate.

Claim 4. (original) A method according to claim 3, further comprising a step of forming a trench isolation surrounding the gate stack, source region and drain region.

Claim 5. (original) A method according to claim 1, further comprising a step of forming a first silicide contact on the first silicon layer.

Claim 6. (original) A method according to claim 1, further comprising a step of forming a second silicide contact on the second silicon layer.

Claim 7. (original) A method according to claim 1, wherein the first silicon layer is epitaxially formed silicon and the second silicon layer is epitaxially grown silicon.

Claim 8. (original) A method according to claim 1, wherein the raised drain region is comprised of a strained silicon layer atop a SiGe layer.

Claim 9. (original) A method according to claim 8, wherein the strained silicon layer is comprised of epitaxially grown silicon.

Claim 10. (original) A method according to claim 1, wherein the raised source region is comprised of a strained silicon layer atop a SiGe layer.

Claim 11. (original) A method according to claim 10, wherein the strained silicon layer is comprised of epitaxially grown silicon.

Claim 12. (canceled)

Claim 13. (currently amended) A method according to claim ~~12~~ 1, further comprising steps of:

- forming a third silicon layer over the cap of the first silicon layer over the raised source region; and

- forming a fourth silicon layer over the cap of the second silicon layer over the raised drain region.

Claim 14. (original) A method according to claim 13, further comprising a step of removing the sacrificial spacers.

Claim 15. (original) A method according to claim 14, wherein the step of removing the sacrificial spacers includes etching away the sacrificial spacers.

Claims 16-28 (cancelled)

Claim 29. (new) A method of fabricating a semiconductor structure, comprising:

- forming a raised source region on a substrate;

- forming a raised drain region on the substrate;

- forming a strained silicon layer on the raised source region and the raised drain region; and

forming a silicon cap on the strained silicon layer.

Claim 30. (new) A method according to claim 29, further comprising forming silicon sidewalls on the raised source region and the raised drain region.

Claim 31. (new) A method according to claim 30, further comprising forming sacrificial spacers along the silicon sidewalls.

Claim 32. (new) A method according to claim 31, further comprising forming a silicon layer on the silicon cap.

Claim 33. (new) A method according to claim 32, further comprising removing the sacrificial spacers.

Claim 34. (new) A method according to claim 33, further comprising forming silicide contacts on the silicon layer.